

SCT4062KRHR

Automotive Grade N-channel SiC power MOSFET

Datasheet

V_{DSS}	1200V
R _{DS(on)} (Typ.)	62mΩ
I _D *1	26A
P_{D}	115W

●Outline



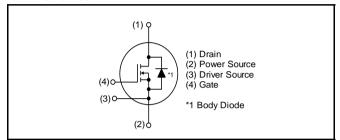
Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

Application

- Automobile
- Switch mode power supplies

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Type	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT4062KR

● **Absolute maximum ratings** (T_{vj} = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	1200	V	
Continuous drain	$V_{GS} = V_{GS_on}$	$T_c = 25^{\circ}C$, , *1	26	А
and source current	V _{GS} = V _{GS_on}	T _c = 100°C	I _D , I _S *1	18	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	$T_c = 25^{\circ}C$	I _{D,pulse} *2	52	Α
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I _{S,pulse} *1,*3	26	Α
Body diode surge forward current V _G		$V_{GS} = 0 V$	I _{S,pulse} *1,*4	52	Α
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V	
Gate - source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		ive voltage	${\sf V_{GS_on}}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V	
Virtual junction temperature		T_{vj}	175	°C	
Range of storage temperature		T_{stg}	-40 to +175	°C	

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol Conditions -		Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown	W	$V_{GS} = 0 \text{ V}, I_D = 5.3 \text{mA}$				V
voltage	V (BR)DSS	$T_{vj} = 25^{\circ}C$	1200	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 1200 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam current		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V , V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current		$V_{GS} = -4V$, $V_{DS} = 0V$	ı	ı	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 6.45 \text{mA}$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 12A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	62	81	mΩ
5 5		T _{vj} = 150°C	-	124	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	4	-	Ω

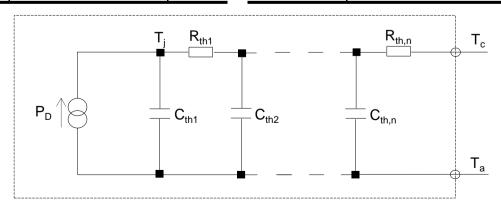
●Thermal resistance

Parameter	Symbol	Values			Unit
Falanielei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}^{^{*9}}$	-	0.98	1.3	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	8.4 ×10 ⁻²	
R _{th2}	4.7 ×10 ⁻¹	K/W
R _{th3}	4.2 ×10 ⁻¹	

Symbol	Value	Unit
C_{th1}	5.3 ×10 ⁻⁴	
C_{th2}	2.4 ×10 ⁻³	Ws/K
C _{th3}	4.3 ×10 ⁻²	



ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

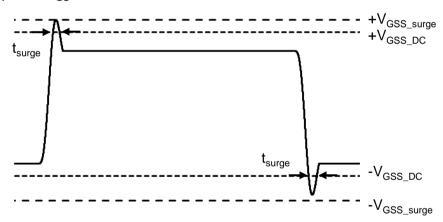
Dovomator	Cymah al	Conditions	Values			l la it
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g _{fs} *8	$V_{DS} = 10V, I_{D} = 12A$	-	6.5	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	1498	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	45	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	3	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 800V$	-	54	-	pF
Total Gate charge	Q _g *8	V _{DS} = 800V	-	64	-	
Gate - Source charge	Q _{gs} *8	$I_D = 12A$ $V_{GS} = 18V$	-	14	-	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	17	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 800V$ $I_{D} = 12A$ $V_{GS} = +18V / 0V$	-	4.4	-	
Rise time	t _r *8		-	11	-	no
Turn - off delay time	t _{d(off)} *8	$R_G = 0\Omega$, L = 250 μ H E_{on} includes diode	-	22	-	ns
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF	-	10		
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	132	•	u l
Turn - off switching loss	E _{off} *8		-	6	ı	μJ
$V_{GS(on)} = +15V$ Short-circuit	- t _{sc} *9	V _{DS} ≤ 800V V _{DS,peak} ≤ 1200V	-	4.5	-	μs
withstand time $V_{GS(on)} = +18V$		$T_{vj(start)} = 25^{\circ}C$ $R_G = 2.2\Omega$	-	4.0	-	μs

●Body diode electrical characteristics (Source-Drain) (T_{vi} = 25°C unless otherwise specified)

Darameter	Cymbal	Conditions	Values			l lmit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_{S} = 12A$	-	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 12A$ $V_R = 800V$	ı	8.1	ı	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 3800A/µs	-	105	-	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	26	ı	Α

^{*1} Limited by maximum T_{vi} and for Max. R_{thJC} .

*5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 The value is based on TO-247 package. Single Pulsed.
- *10 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

^{*2} Pulse width and duty cycle are limited by $T_{v_j,max}$.

^{*3} Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%

^{*4} When used as a protective function, PW ≤ 10µs

Fig.1 Power Dissipation Derating Curve

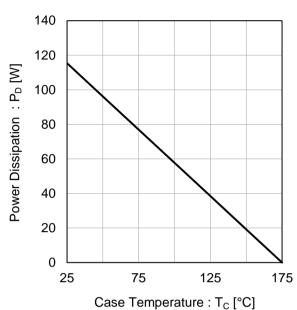


Fig.2 Maximum Safe Operating Area

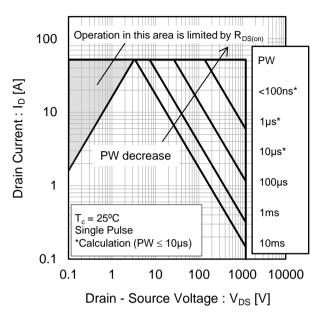
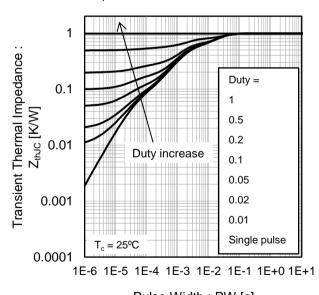


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]

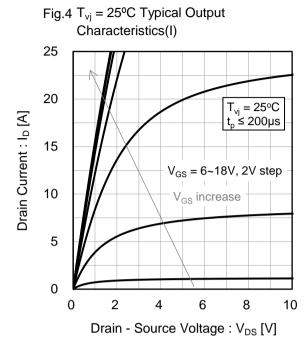
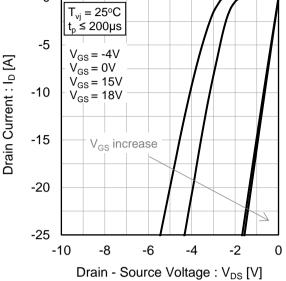
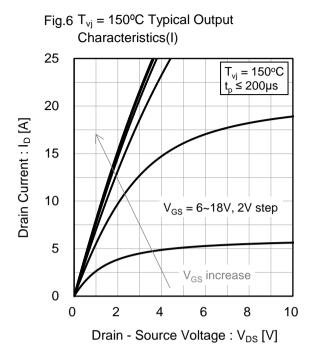
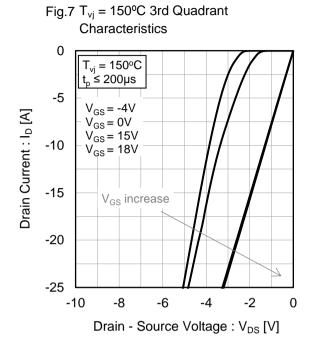


Fig.5 $T_{vj} = 25^{\circ}$ C 3rd Quadrant Characteristics



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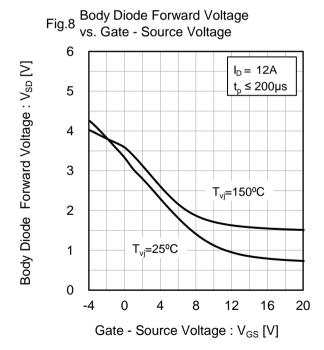


Fig.9 Typical Transfer Characteristics (I)

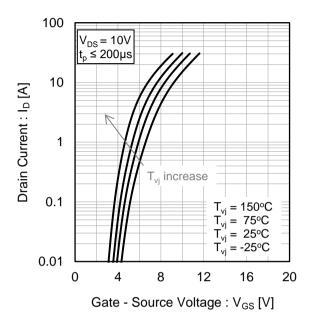


Fig.10 Typical Transfer Characteristics (II)

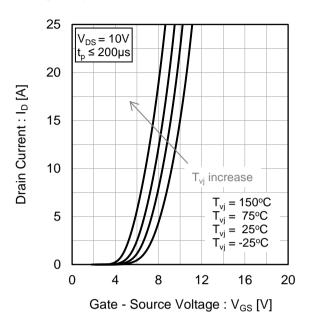


Fig.11 Gate Threshold Voltage vs. Virtual Junction Temperature

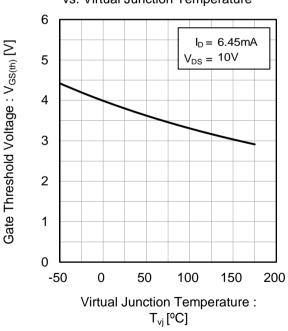


Fig.12 Transconductance vs. Drain Current

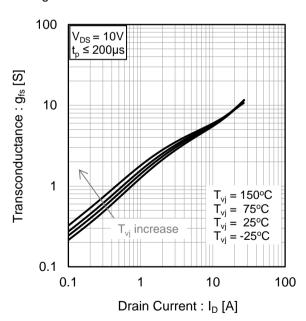


Fig.13 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

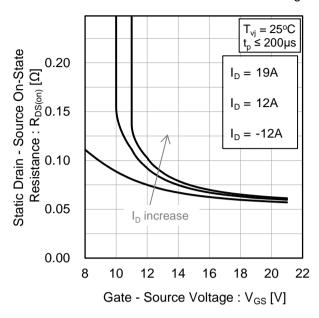


Fig.14 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

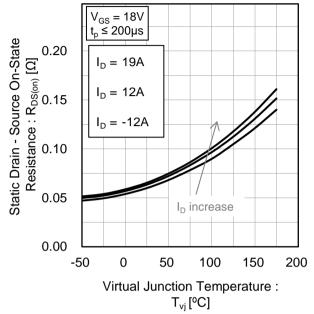


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current

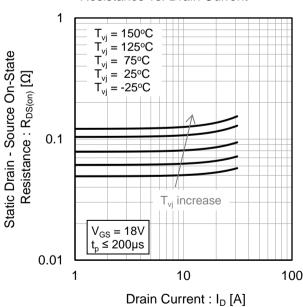
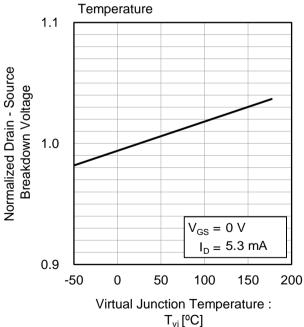
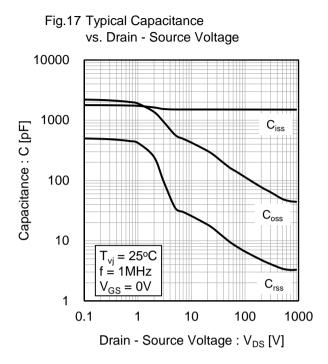


Fig.16 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction





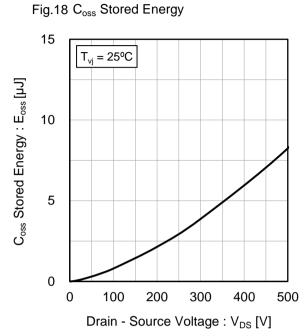


Fig.19 Dynamic Input Characteristics

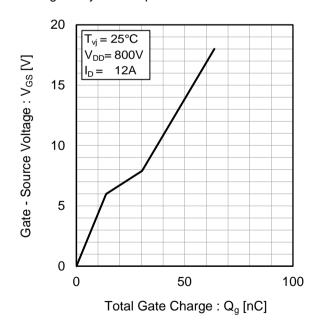
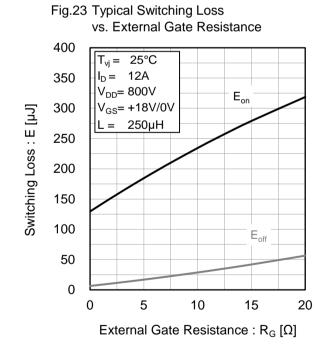


Fig.20 Typical Switching Time vs. External Gate Resistance 80 $T_{vi} = 25^{\circ}C$ 12A $t_{d(off)}$ V_{DD}= 800V 60 V_{GS}= +18V/0V Switching Time: t [ns] $L = 250 \mu H$ 40 $t_{d(on)}$ 20 i t_r t_f 0 5 10 15 20

External Gate Resistance : $R_G[\Omega]$

Fig.21 Typical Switching Loss vs. Drain - Source Voltage 400 $T_{vi} = 25^{\circ}C$ 350 12A V_{GS}= +18V/0V Switching Loss: E [µJ] 300 $R_G = 0\Omega$ $L = 250 \mu H$ 250 200 150 E_{on} 100 50 0 100 200 300 400 500 600 700 800 Drain - Source Voltage: V_{DS} [V]

Fig.22 Typical Switching Loss vs. Drain Current 400 $T_{vj} =$ 25°C $V_{DD} = 800V$ 350 $V_{GS} = +18V/0V$ 300 $R_G = 0\Omega$ Switching Loss: E [µJ] 250µH L = 250 E_{on} 200 150 100 50 0 0 5 10 15 20 25 Drain Current: I_D [A]



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Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

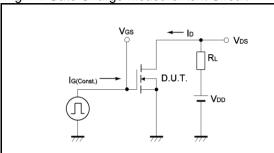


Fig.2-1 Switching Characteristics Measurement Circuit

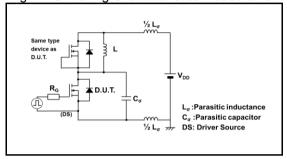


Fig.2-3 Waveforms for Switching Energy Loss

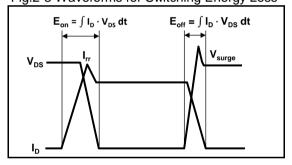


Fig.3-1 Reverse Recovery Time Measurement Circuit

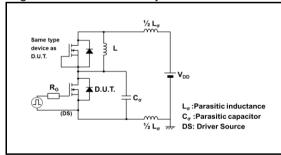


Fig.1-2 Gate Charge Waveform

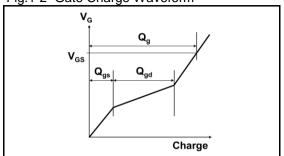


Fig.2-2 Waveforms for Switching Time

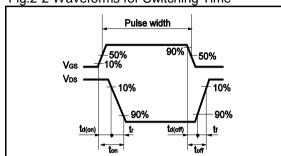
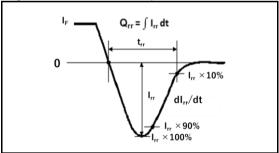
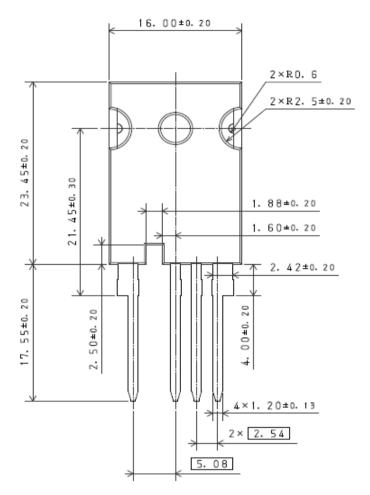
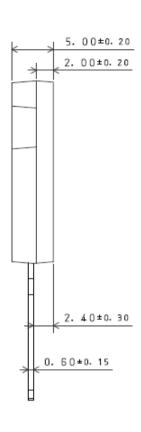


Fig.3-2 Reverse Recovery Waveform

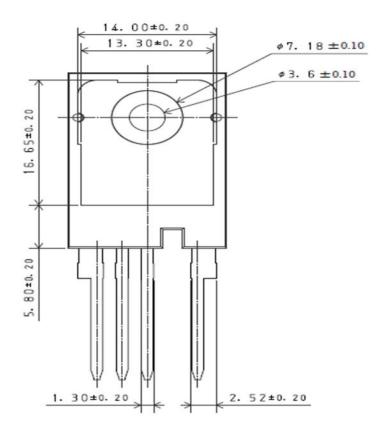


●Package Dimensions



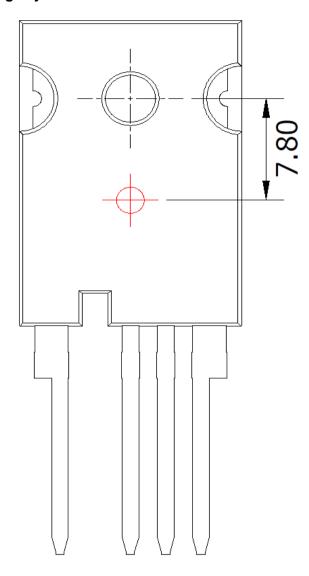


Unit: mm



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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